	Туре	L#	Hits	Search Text	DBs	Time Stamp	C o m m	ef in	ro
1	BRS	L8	21	(sti or trench) same (wet etch\$3) same ((round adj bottom) and (round corner))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/01 13:47		!	0
2	BRS	L15	95	(sti or trench) and (wet etch\$3) and ((round adj bottom) and (round corner))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/01 13:48		:	0
3	BRS	L22	74	15 not 8	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/01 14:22			0
4	BRS	L64	20	@pd<=19991228 AND 57	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/01 19:03	:	.	0
5	BRS	L78	12	clean\$3 with ((CF4 or "CF.sub.4") and (Ar or argon)) with (semiconductor or substrate or wafer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/01 17:51		.!	0
6	BRS	L85	1102	((arc or antireflect\$3) with nitride) and etch\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/01 17:51		!	0
7	BRS	L92	0	((arc or antireflect\$3) with "on nitride") and etch\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/01 18: 4 7	:	1	0
8	BRS	L99	0	((arc or antireflect\$3) near5 "on nitride") and etch\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/01 17: 44		(0

	Туре	L#	Hits	Search Text	DBs	Time Stamp	C o m e i	ef r	0
9	BRS	L106	638	85 and 438/\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/01 17:56	•)
10	BRS	L113	197	106 and @pd<=20000810	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/01 17:56		C)
11	BRS	L120		85 and (("CF.sub.4" or "CHF.sub.3" or "CH.sub.2 F.sub.2" or "CH.sub.3 F") same ("O.sub.2" or O2 or oxygen) same (Ar or argon or Kr or krypton or Xe or xenon or Ne or neon))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/01 18:47		C)
12	BRS	L127	4 7	120 and 438/\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/01 17:56		C)
13	BRS	L134	7	127 and @pd<=20000810	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/01 17:56		:0	
14	BRS	L141	21	F") with ("O.sub.2" or O2 or oxygen) with (Ar or argon or Kr or	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/01 18:55		C	